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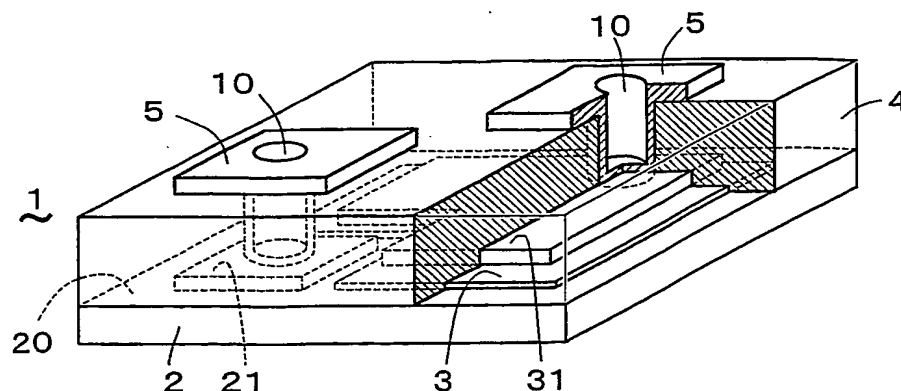
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(54) Title: SEMICONDUCTOR LIGHT-EMITTING DEVICE AND ITS MANUFACTURING METHOD



(57) Abstract: In a light-emitting device and its manufacturing method, mounting by batch process with surface-mount technology, high light extraction efficiency, and low manufacturing cost are realized. The light-emitting device 1 comprises semiconductor layers (2, 3) of p-type and n-type nitride semiconductor, semiconductor-surface-electrodes (21, 31) to apply currents into each of the semiconductor layers (2, 3), an insulating layer 4 which holds the semiconductor layers (2, 3), and mount-surface-electrodes (5). The semiconductor layers (2) has a non-deposited area 20 where the other semiconductor layer (3) is not deposited. The insulating layer (4) has VIA 10 which electrically connect the mount-surface-electrodes 5 and the semiconductor-surface-electrodes (21, 31). In the manufacturing process, firstly, semiconductor layers (2, 3) and semiconductor-surface-electrodes (21, 31) are deposited on the transparent crystal substrate, and by using build-up process, insulating layer (4) and the mount-surface-electrodes (5) are formed, and secondly, VIA 10 are formed, and finally, the transparent crystal substrate is separated to get light-emitting device (1). Light can be extracted directly and efficiently from the semiconductor layers (2, 3). With the mount-surface-electrodes (21, 31), light-emitting device (1) can be mounted by using surface mount technology.

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